

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claim 1 (previously presented): A sputtering target comprising a target containing at least Co, Cr, Pt and B and having a target surface prepared by melting and rolling in which intermetallic compounds, oxides, carbides, carbonitrides and other substances without ductility exist in a highly ductile matrix phase of said sputtering target at a volume ratio of 1 to 50%, said substances without ductility being of a size in which an average particle diameter is at least 0.5 to 50 μ m, a Vickers hardness of said highly ductile matrix phase being 400 or less, a Vickers hardness of said substances without ductility being 400 or more, and a hardness difference thereof being at least 1.5 times, wherein defects of 10 μ m or more resulting from machine work do not exist.

Claims 2-3 (canceled).

Claim 4 (previously presented): A surface processing method for a sputtering target, comprising the steps of:

preparing a target surface of a sputtering target containing at least Co, Cr, Pt and B by melting and rolling in which intermetallic compounds, oxides, carbides, carbonitrides and other substances without ductility exist in a highly ductile matrix phase of said target at a volume ratio of 1 to 50%, said substances without ductility being of a size in which an average

particle diameter is at least 0.5 to 50 μm , a Vickers hardness of said highly ductile matrix phase being 400 or less, a Vickers hardness of said substances without ductility being 400 or more, and a hardness difference thereof being at least 1.5 times; preliminarily subjecting said target to primary processing of cutting work by cutting a thickness of 1mm to 10mm from said target surface; and then subsequently finish processing said target via polishing a thickness of 1 μm to 50 μm from said target surface after said primary processing such that defects of 10 μm or more resulting from machine work do not exist.

Claims 5-10 (canceled).

Claim 11 (previously presented): A surface processing method according to claim 4, wherein said polishing is performed with sandpaper or a grindstone having a rough abrasive grain size of #80 to #400.

Claim 12 (previously presented): A surface processing method according to claim 4, wherein said cutting is performed with lathe processing employing a cutting tool or a chip.

Claim 13 (currently amended): A sputtering target, comprising:
a sputtering target body prepared by melting and rolling and containing at least
Co, Cr, Pt and B;

said sputtering target body having a surface including particles of intermetallic compounds, oxides, carbides, and carbonitrides existing within a highly ductile matrix phase at a volume ratio of 1 to 50%;

 said particles of intermetallic compounds, oxides, carbides, and carbonitrides having an average particle diameter of at least 0.5 μ m;

 said matrix phase having a Vickers hardness of 400 or less, said particles of intermetallic compounds, oxides, carbides, and carbonitrides having a Vickers hardness of 400 or more, and a hardness difference thereof being at least 1.5 times; and

 surface defects of 10 μ m or more resulting from machine work performed on said sputtering target body do not exist on said surface and said surface provides a flat and smooth target face without undulation.

Claim 14 (previously presented): A sputtering target according to claim 13, wherein said average particle diameter of said intermetallic compounds, oxides, carbides, and carbonitrides is 0.5 to 50 μ m.

Claim 15 (previously presented): A sputtering target according to claim 14, wherein said intermetallic compounds, oxides, carbides, and carbonitrides are less ductile than said matrix phase.

Claim 16 (previously presented): A sputtering target according to claim 14, wherein said intermetallic compounds, oxides, carbides, and carbonitrides are without ductility.

Claim 17 (currently amended): A method of processing a surface of a sputtering target, comprising the steps of:

melting and rolling raw material containing at least Co, Cr, Pt and B to form a sputtering target having a surface with particles of intermetallic compounds, oxides, carbides, and carbonitrides existing within a highly ductile matrix phase at a volume ratio of 1 to 50%, the intermetallic compounds, oxides, carbides, and carbonitrides having an average particle diameter of at least $0.5\mu\text{m}$ and a Vickers hardness of 400 or more, the matrix phase having a Vickers hardness of 400 or less, and a hardness difference thereof being at least 1.5 times;

preliminarily subjecting said sputtering target to primary processing of cutting work by cutting 1mm to 10mm of depth from said target surface; and then subsequently finish processing said sputtering target via polishing 1 μm to 50 μm of depth from said surface after said primary processing such that surface defects of 10 μm or more resulting from machine work do not exist and such that the target surface provides a flat and smooth target face without undulation.